

BC212L



TO-92

PNP General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300mA. Sourced from Process 68.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	50	V	
V _{CBO}	Collector-Base Voltage	60	V	
V _{EBO}	Emitter-Base Voltage	5	V	
Ic	Collector Current - Continuous	300	mA	
T _{J, Tstg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

 $^{^{\}star}$ These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 $^{\circ}\text{C}.$
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_{A = 25°C unless otherwise noted}

Symbol	Characteristic	Max	Units
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R _θ JC	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		°C/W

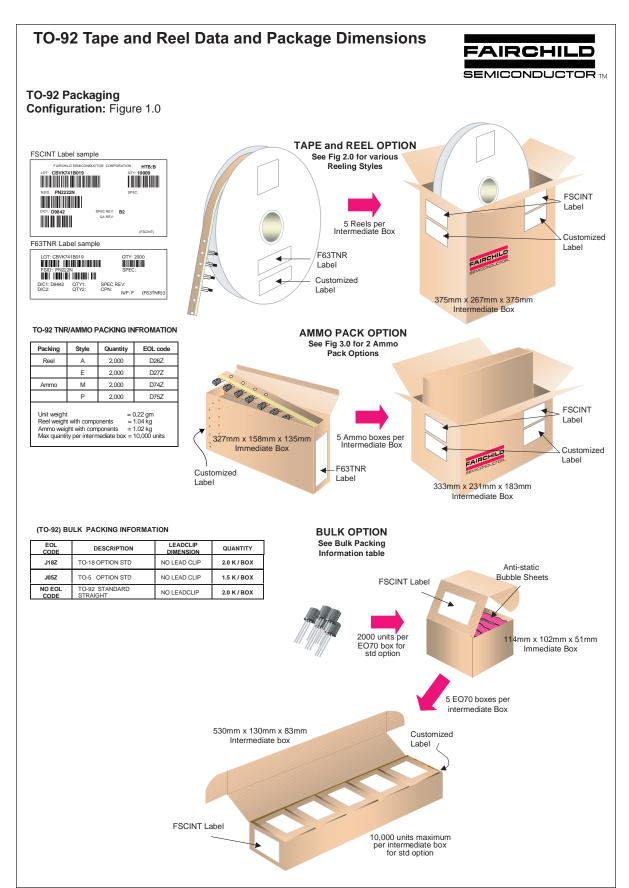
PNP General Purpose Amplifier (continued)

Electrical Characteristics

T_{A = 25°C} unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 2 mA	50		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 10 μA	60		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 10 μA	5		V
СВО	Collector Cutoff Current	V _{CB} = 30V		15	nA
ЕВО	Emitter Cutoff Current	V _{EB} = 4V		15	nA
ON CHAR	ACTERISTICS*				
h _{FE}	DC Current Gain	$I_C = 10 \text{ uA}, V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$	40 60	300	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 100 mA, I _B = 5 mA		0.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 100 mA, I _B = 5 mA		1.1	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 2 mA, V _{CE} = 5 V	0.6	0.72	V
SMALL SI	GNAL CHARACTERISTICS			1	
C _{ob}	Output Capacitance	V _{CB} = 10 V, f = 1.0 MHz		10	pF
h _{fe}	Small Signal Current Gain	$I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f=1 \text{kHz}$	60		-
NF	Noise Figure	I _C = 200 uA,V _{CE} = 5 V, f=1kHz, Rg=2KOhms,BW=200Hz		10	dB
fΤ	Current Gain-Bandwidth Product	VCE=5V, IC=10mA,f=100MHz	200		MHz

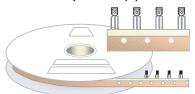
*Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%



TO-92 Tape and Reel Data and Package Dimensions, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

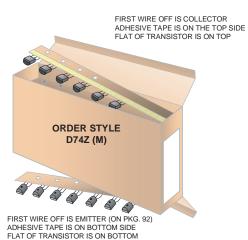


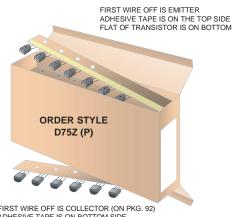
Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

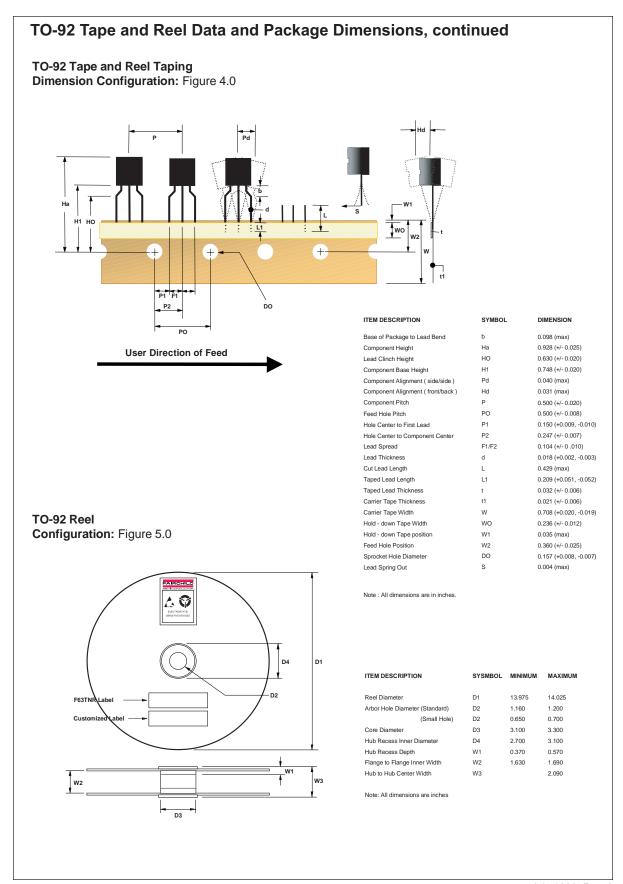
Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP



TO-92 Tape and Reel Data and Package Dimensions TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 96 94 В В 0.76 В G Ε Ø0.060 [Ø1.52] 0.010 [0.254] DEEP В S С 0.615 0.570 5.0°TYP.

January 2000, Rev. B

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

FACT™ QFET™ FACT Quiet Series™ QS™

FAST[®] Quiet Series[™] SuperSOT[™]-3 GTO[™] SuperSOT[™]-6

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.